

a 2004 0096

The invention refers to the optoelectronics, in particular to the lens with refractive index gradient.

Summary of the invention consists in that into a semiconductor substrate there are implanted ions with a dose of high energy, determined by the relation:

$$D=\alpha R^2,$$

where:

D – the dose of high energy of the implanted ions,

R – the distance from the centre up to the substrate periphery,

α – the dose gradient,

then it is carried out the electrochemical pickling.

Claims: 1

Fig.: 1